



CSD19538Q2T Information



For Reference Only

Part Number CSD19538Q2T **Manufacturer** Texas Instruments

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET NCH 100V 13.1A 6WSON

Package 6-WDFN Exposed Pad

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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CSD19538Q2T Specifications

| Manufacturer Part Number CSD19538Q2T Manufacturer Texas Instruments Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 6-WDFN Exposed Pad Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.8V @ 250µA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | | |
|---|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 6-WDFN Exposed Pad Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 15.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Sym Ohm @ 5A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case PowDFN Exposed Pad | Manufacturer Part Number | CSD19538Q2T |
| Package 6-WDFN Exposed Pad Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.8V @ 250μA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Manufacturer | Texas Instruments |
| Package 6-WDFN Exposed Pad Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.8V @ 250μA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Category | Discrete Semiconductor Products |
| Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.8V @ 250μA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | | Transistors - FETs, MOSFETs - Single |
| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.8V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds454pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 20.2W (Tc)Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | Package | 6-WDFN Exposed Pad |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.8V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds454pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 20.2W (Tc)Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | Series | NexFET? |
| Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.8V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds454pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 20.2W (Tc)Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.8V @ 250μA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 6-WSON (2x2) Package / Case | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.8V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds454pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 20.2W (Tc)Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | Drain to Source Voltage (Vdss) | 100V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Current - Continuous Drain (Id) @ 25°C | 13.1A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 454pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 5.6nC @ 10V 454pF @ 50V 454pF @ | Drive Voltage (Max Rds On, Min Rds On) | 6V, 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Vgs(th) (Max) @ Id | 3.8V @ 250µA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 20.2W (Tc)Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | Gate Charge (Qg) (Max) @ Vgs | 5.6nC @ 10V |
| FET Feature - Power Dissipation (Max) 2.5W (Ta), 20.2W (Tc) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Input Capacitance (Ciss) (Max) @ Vds | 454pF @ 50V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 59 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs59 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | FET Feature | - |
| Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Power Dissipation (Max) | 2.5W (Ta), 20.2W (Tc) |
| Mounting TypeSurface MountSupplier Device Package6-WSON (2x2)Package / Case6-WDFN Exposed Pad | Rds On (Max) @ Id, Vgs | 59 mOhm @ 5A, 10V |
| Supplier Device Package 6-WSON (2x2) Package / Case 6-WDFN Exposed Pad | Operating Temperature | -55°C ~ 150°C (TJ) |
| Package / Case 6-WDFN Exposed Pad | Mounting Type | Surface Mount |
| · | Supplier Device Package | 6-WSON (2x2) |
| Report errors? | Package / Case | 6-WDFN Exposed Pad |
| | | Report errors? |

CSD19538Q2T Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

CSD19538Q2T Payment Methods



















CSD19538Q2T Shipping Methods













If you have any question about CSD19538Q2T, please do not hesitate to contact us!

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